

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	480	plasma.ti,ab,clm. and ((resistor) near3 (electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:14
L2	99	(plasma and etch\$4).ti,ab,clm. and ((resistor) near3 (electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:17
L3	71	(1 not 2) and etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:22
L4	310	1 not 2 not 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:22
S10	71	(156/345.45).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/14 14:13
S11	290	(156/345.47).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/02 17:06
S12	158	(156/345.44).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/02 17:07
S13	269	(156/345.43).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/02 17:48

S18	104	(156/345.54).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 20:01
S36	184591	plasma	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 20:34
S37	3140	S36 and ((ground\$3 protect\$4 charg\$4) near5 (substrate workpiece target wafer))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 12:31
S38	97	S37 and (resistor diode)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 12:31
S39	60803	plasma	JPO	OR	ON	2005/02/03 20:37
S40	29	S39 and (diode near5 (substrate workpiece target))	JPO	OR	ON	2005/02/03 20:37
S41	29	S37 and ((reflector three third) near5 (electrode))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 20:44
S42	60803	plasma	JPO	OR	ON	2005/02/04 12:31
S43	1260	S42 and ((ground\$3 protect\$4 charg\$4) near5 (substrate workpiece target wafer))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 12:31
S44	560	S43 and electrode	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 12:31
S45	184591	plasma	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 12:31
S46	3140	S45 and ((ground\$3 protect\$4 charg\$4) near5 (substrate workpiece target wafer))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 12:31
S47	97	S46 and (resistor diode)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 12:31
S48	544	S44 not S47	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 13:39
S49	425	(156/345.51).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 13:40

S50	3002	(118/(719,723E,723R,729)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 13:41
S51	2138	S50 and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 13:41
S52	704	S51 and ((ground\$3 protect\$4 charg\$4) near5 (substrate workpiece target wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 13:41
S67	207	(118/723ER).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 14:28
S68	1419	(118/723E).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 14:27
S69	873	S68 not S67 not S52	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 14:42
S71	778	S69 and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 14:43
S72	683	S71 and electrode\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 14:44

S74	618272	(("118") or ("156") or ("216") or ("438") or ("427") or ("315")).CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 18:55
S78	35427	S74 and plasma.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 18:58
S80	3353	S78 and ((ground\$3 protect\$4 charg\$4) near2 (substrate workpiece target wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 16:35
S81	724	S80 and ((power active activate charg\$3) near2 electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 18:59
S84	431	S80 and ((resistor diode power supply) near2 (substrate workpiece target wafer)) not S81	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 19:29
S85	119	S80 and ((connect\$4 conduct\$4 wire\$1 wiring) near2 (substrate workpiece target wafer) near5 (resistor diode power supply)) not S81	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 19:30
S87	369	S84 not S85	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 19:47
S88	32498	shimadzu.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 16:35

S89	63	S88 and ((ground\$3 protect\$4 charg\$4) near2 (substrate workpiece target wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 16:36
S90	19	S89 and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 17:26
S91	787	S88 and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 17:27
S92	189	S91 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 17:27
S93	97	(NODA-YOSHIAKI NODA-YOSHIAKI-NARASHINODAI HIYAMA-MICHYUKI TAKIMOTO-KATSUHIDE TAKIMOTO-KATSUHIKO TAKIMOTO-KATSUHISA TAKIMOTO-KATSUYASU TAKIMOTO-KATSUYOSHI).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 17:27
S94	178	S92 not S93 not S90	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 17:27
S95	93	plasma.ti,ab,clm. and ((diode rectifi\$4 bias) near2 (connect\$3 path wired) near2 (substrate workpiece target wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 18:33
S97	5879	plasma.ti,ab,clm. and (((three third) near2 electrode) or triode or reflector)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 18:34

S98	97	plasma.ti,ab,clm. and (((three third) near2 electrode) or triode) and reflector	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 11:15
S10 3	1795	(315/241R).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 16:59
S10 4	57	S103 and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 16:56
S10 5	700	(315/171).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 16:59
S10 6	510	(315/173).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 16:59
S10 7	26	(S105 S106) and plasma not S104	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 16:59
S10 8	168220	"427"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:05
S10 9	4035	S108 and (substrate workpiece target wafer) near2 (charg\$4 power bias potential anode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:11
S11 0	179	S108 and (substrate workpiece target wafer) near2 (charg\$4 power bias potential anode)	JPO	OR	ON	2005/02/07 17:06

S11 1	54	S110 and plasma	JPO	OR	ON	2005/02/07 17:06
S11 2	2197	S109 and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:12
S11 3	618272	(("118") or ("156") or ("216") or ("438") or ("427") or ("315")).CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 17:12
S11 4	35427	S113 and plasma.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:12
S11 5	3353	S114 and ((ground\$3 protect\$4 charg\$4) near2 (substrate workpiece target wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:13
S11 6	724	S115 and ((power active activate charg\$3) near2 electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:12
S11 7	2087	S112 not S116	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:13
S11 8	763	S117 and ((resistor resistance diode rectif\$4 bias) near2 (substrate workpiece target wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:15
S11 9	743	S118 not S111	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:14

S12 0	126	S117 and ((resistor resistance diode rectif\$4) near2 (substrate workpiece target wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:22
S12 1	618	S119 not S120	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:48
S12 2	5	plasma.ti,ab,clm. and (((resistor resistance resistive) near2 (series direct) near5 (power supply ac dc rf)) with (substrate target workpiece wafer))	US-PGPUB; USPAT	OR	ON	2005/02/07 17:50
S12 3	1	plasma.ti,ab,clm. and (reflector with electrode with float\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 16:47
S12 4	192	plasma.ti,ab,clm. and (reflector with electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 16:48
S12 5	13	plasma.ti,ab,clm. and (reflect\$3 with electrode with float\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 16:52
S12 6	1960	plasma.ti,ab,clm. and (reflect\$3 with electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 16:53
S12 7	35	plasma.ti,ab,clm. and (reflect\$3 near5 electrode) and (electrode near5 float\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 16:53
S12 8	25	S127 not S125	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 16:53

S12 9	88	(156/345.3).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/10 14:07
S13 0	242	plasma.ti,ab,clm. and ((chamber) near5 (liner shield cover) near5 (insulat\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/10 14:46
S13 1	9	plasma.ti,ab,clm. and ((electrode ring) near5 (confinement confin\$3 reflect\$4) near5 (float\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/10 14:48